

Silicon NPN Power Transistors

BU2520DW

DESCRIPTION

- With TO-247 package
- High voltage,high speed
- Built-in damper diode

APPLICATIONS

- For use in horizontal deflection circuits of large screen colour TV receivers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

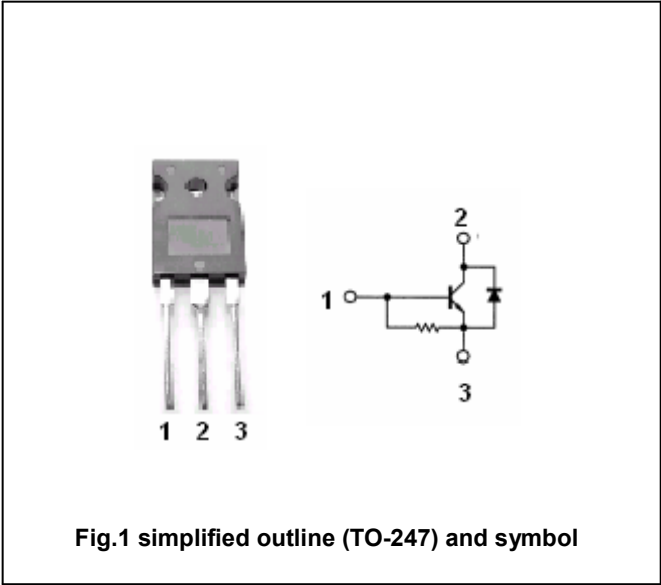


Fig.1 simplified outline (TO-247) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
I_C	Collector current (DC)		10	A
I_{CM}	Collector current-peak		25	A
I_B	Base Collector current (DC)		6	A
I_{BM}	Base current-peak		9	A
P_{tot}	Total power dissipation	$T_C=25^{\circ}C$	125	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$, $L=25mH$	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=600mA$; $I_C=0$	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A$; $I_B=1.2A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A$; $I_B=1.2A$			1.1	V
I_{CES}	Collector cut-off current	$V_{CE}=BV_{CES}$; $V_{BE}=0$ $T_C=125^\circ C$			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7.5V$; $I_C=0$	100		300	mA
h_{FE-1}	DC current gain	$I_C=1.0A$; $V_{CE}=5V$		13		
h_{FE-2}	DC current gain	$I_C=6A$; $V_{CE}=5V$	5	7	9.5	
V_F	Diode forward voltage	$I_F=6A$			2.2	V
C_C	Collector capacitance	$f=1MHz$; $V_{CB}=10V$		115		pF

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